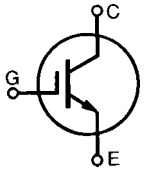
IXYS

HiPerFAST™ IGBT IXGR 24N60C
ISOPLUS247™
(Electrically Isolated Back Surface)

V_{CES} = 600 V
I_{C25} = 42 A
$V_{CE(sat)}$ = 2.5 V
$t_{fi(typ)}$ = 60 ns

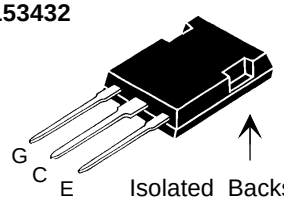
Preliminary data sheet



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 150°C	600	V
V_{CGR}	T_J = 25°C to 150°C; R_{GE} = 1 MΩ	600	V
V_{GES}	Continuous	±20	V
V_{GEM}	Transient	±30	V
I_{C25}	T_C = 25°C	42	A
I_{C110}	T_C = 110°C	22	A
I_{CM}	T_C = 25°C, 1 ms	80	A
SSOA (RBSOA)	V_{GE} = 15 V, T_{VJ} = 125°C, R_G = 22 Ω Clamped inductive load, L = 100 µH	I_{CM} = 48 @ 0.8 V_{CES}	A
P_C	T_C = 25°C	80	W
T_J		-40 ... +150	°C
T_{JM}		150	°C
T_{stg}		-40 ... +150	°C
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	°C
V_{ISOL}	50/60 Hz, RMS, t = 1minute leads-to-tab	2500	V
Weight		5	g

Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
BV_{CES}	I_C = 250 µA, V_{GE} = 0 V	600			V
$V_{GE(th)}$	I_C = 250 µA, V_{CE} = V_{GE}	2.5		5.0	V
I_{CES}	V_{CE} = 0.8 • V_{CES} T_J = 25°C V_{GE} = 0 V T_J = 150°C			200 1	µA mA
I_{GES}	V_{CE} = 0 V, V_{GE} = ±20 V			±100	nA
$V_{CE(sat)}$	I_C = I_T, V_{GE} = 15 V (see note 1)		2.1	2.5	V

ISOPLUS 247
E153432



G = Gate, C = Collector
E = Emitter

* Patent pending

Features

- DCB Isolated mounting tab
- Meets TO-247AD package Outline
- High current handling capability
- Latest generation HDMOS™ process
- MOS Gate turn-on
  - drive simplicity

Applications

- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- AC motor speed control
- DC servo and robot drives
- DC choppers

Advantages

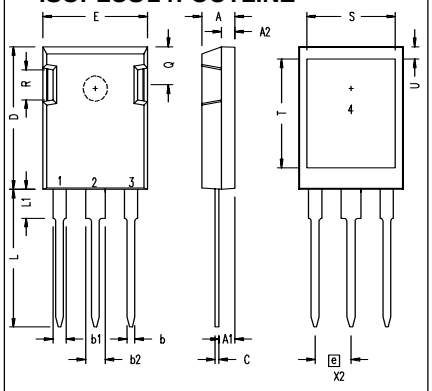
- Easy assembly
- High power density
- Very fast switching speeds for high frequency applications

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Symbol	Test Conditions	Characteristic Values (T_J = 25°C, unless otherwise specified) min.	typ.	max.	
g_{fs}	$I_C = I_T$; V_{CE} = 10 V, Pulse test, t ≤ 300 µs, duty cycle ≤ 2 %	9	17		S
C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		1500		pF
C_{oes}			120		pF
C_{res}			40		pF
Q_g	$I_C = I_T$, V_{GE} = 15 V, V_{CE} = 0.5 V_{CES}		55		nC
Q_{ge}			13		nC
Q_{gc}			17		nC
$t_{d(on)}$	**Inductive load, T_J = 25°C**		15		ns
t_{ri}	$I_C = I_T$, V_{GE} = 15 V		25		ns
$t_{d(off)}$	V_{CE} = 0.8 V_{CES}, $R_G = R_{off}$ = 18 Ω		75	140	ns
t_{fi}	Remarks: Switching times may increase for V_{CE} (Clamp) > 0.8 V_{CES}, higher T_J or increased R_G		60	110	ns
E_{off}			0.24	0.36	mJ
$t_{d(on)}$	**Inductive load, T_J = 125°C**		15		ns
t_{ri}	$I_C = I_T$, V_{GE} = 15 V		12		ns
E_{on}	V_{CE} = 0.8 V_{CES}, $R_G = R_{off}$ = 18 Ω		0.15		mJ
$t_{d(off)}$	Remarks: Switching times may increase for V_{CE} (Clamp) > 0.8 V_{CES}, higher T_J or increased R_G		130		ns
t_{fi}			110		ns
E_{off}			0.6		mJ
R_{thJC}				1.57	K/W
R_{thCK}			0.15		K/W

Note: 1. I_T = 24A

ISOPLUS 247 OUTLINE





1 Gate, 2 Drain (Collector)
3 Source (Emitter)
4 no connection

Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.83	5.21	.190	.205
A_1	2.29	2.54	.090	.100
A_2	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b_1	1.91	2.13	.075	.084
b_2	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	.244
R	4.32	4.83	.170	.190

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1 4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025